

Transistors

# 4V Drive Pch MOS FET

## RSF010P03

●Structure

Silicon P-channel MOS FET

●Features

- 1) Low on-resistance.
- 2) High speed switching.

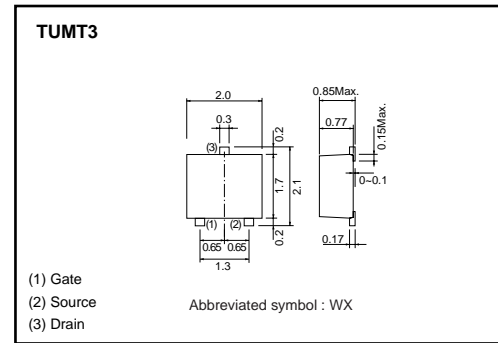
●Applications

Switching

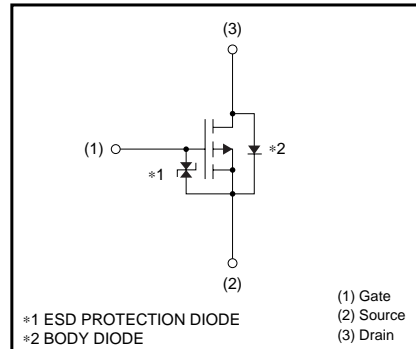
●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RSF010P03		○

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V <sub>DSS</sub>	-30	V	
Gate-source voltage	V <sub>GSS</sub>	±20	V	
Drain current	Continuous	I <sub>D</sub>	±1	A
	Pulsed	I <sub>DP</sub> *1	±4	A
Source current (Body diode)	Continuous	I <sub>S</sub>	-0.3	A
	Pulsed	I <sub>SP</sub> *1	-4	A
Total power dissipation	P <sub>D</sub> *2	0.8	W	
Channel temperature	T <sub>ch</sub>	150	°C	
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C	

\*1 Pw≤10μs, Duty cycle≤1%  
\*2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	R <sub>th(ch-a)</sub> *	156	°C/W

\* Mounted on a ceramic board

## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR) DSS}$	–30	–	–	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	–1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	–1.0	–	–2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	250	350	mΩ	$I_D = -1A, V_{GS} = -10V$
		–	400	560	mΩ	$I_D = -0.5A, V_{GS} = -4.5V$
		–	450	630	mΩ	$I_D = -0.5A, V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} $ *	0.5	–	–	S	$V_{DS} = -10V, I_D = -0.5A$
Input capacitance	$C_{iss}$	–	120	–	pF	$V_{DS} = -10V$
Output capacitance	$C_{oss}$	–	27	–	pF	$V_{GS} = 0V$
Reverse transfer capacitance	$C_{rss}$	–	17	–	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	8	–	ns	$V_{DD} = -15V$
Rise time	$t_r$ *	–	11	–	ns	$I_D = -0.5A$
Turn-off delay time	$t_{d(off)}$ *	–	20	–	ns	$V_{GS} = -10V$
Fall time	$t_f$ *	–	12	–	ns	$R_L = 30\Omega$ $R_G = 10\Omega$
Total gate charge	$Q_g$	–	1.9	–	nC	$V_{DD} = -15V, V_{GS} = -5V$
Gate-source charge	$Q_{gs}$	–	0.7	–	nC	$I_D = -1A$
Gate-drain charge	$Q_{gd}$	–	0.4	–	nC	$R_L = 15\Omega, R_G = 10\Omega$

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}$	–	–	–1.2	V	$I_S = -0.3A, V_{GS} = 0V$

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